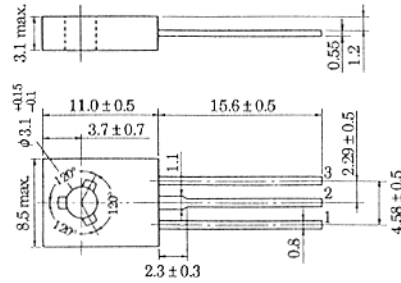


2SC2611

SILICON NPN TRIPLE DIFFUSED
HIGH VOLTAGE AMPLIFIER
TV VIDEO OUTPUT



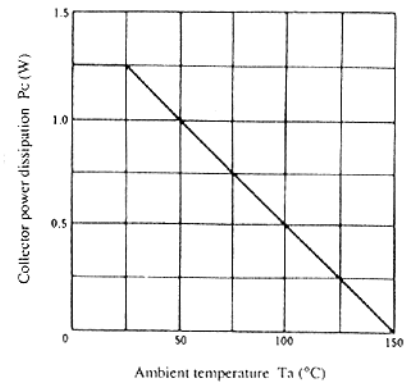
1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

(JEDEC TO-126 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2611	Unit
Collector to base voltage	V _{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector power dissipation	P _C	1.25	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

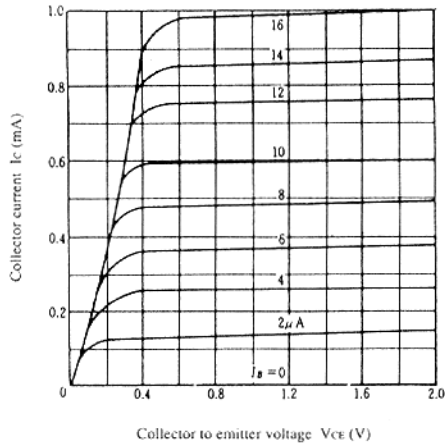
MAXIMUM COLLECTOR DISSIPATION CURVE



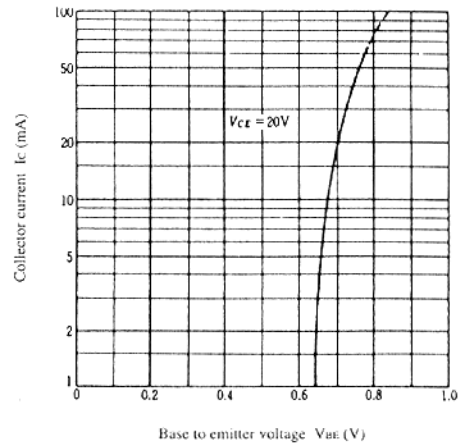
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	300	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	300	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5	—	—	V
Collector cutoff current	I _{CEO}	V _{CE} = 250V, R _{BE} = ∞	—	—	1.0	μA
DC current transfer ratio	h _{FE}	V _{CE} = 20V, I _C = 20mA	30	—	200	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 20mA, I _B = 2mA	—	—	1.5	V
Gain bandwidth product	f _T	V _{CE} = 20V, I _C = 20mA	50	80	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 20V, I _E = 0, f = 1MHz	—	—	4.0	pF

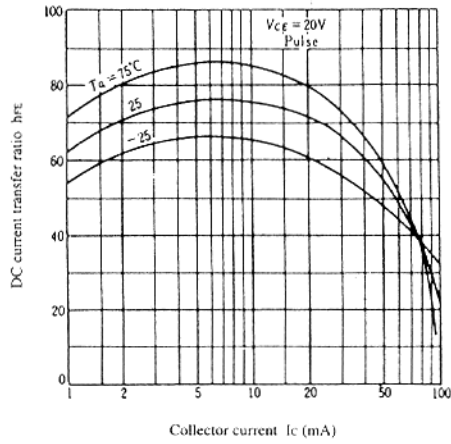
TYPICAL OUTPUT CHARACTERISTICS



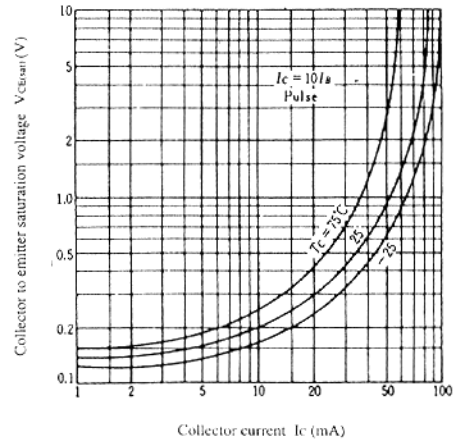
TYPICAL TRANSFER CHARACTERISTICS



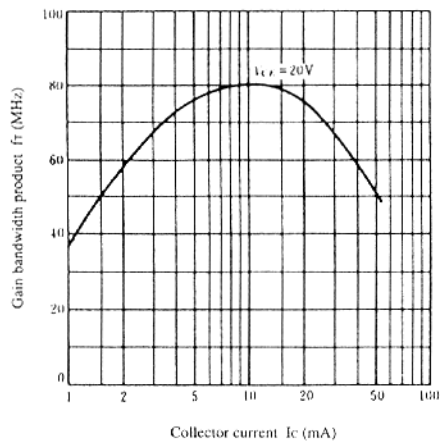
DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



COLLECTOR TO EMITTER SATURATION VOLTAGE VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE

